

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-HFA70FA120</u>

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Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VS-HFA70FA120 - DIODE HEXFRED 70A 1200V SOT-227

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VS-HFA70FA120

RoHS

COMPLIANT

Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 70 A



PRODUCT SUMMARY					
V_{R}	1200 V				
V _F (typical)	2.3 V				
t _{rr} (typical)	51 ns				
$I_{F(AV)}$ per module at T_C	70 A at 94 °C				
Package	SOT-227				

FEATURES

- · Fast recovery time characteristic
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL approved file E78996



· Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

The dual diode series configuration (VS-HFA70FA120) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_R		1200	V	
Continuous forward current per leg	IF	T _C = 110 °C	35	А	
Single pulse forward current per leg	I _{FSM}	T _J = 25 °C	380	Α .	
Maximum power dissipation per module	P _D	T _C = 110 °C	174	W	
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V	
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-		
Forward voltage		I _F = 30 A	-	2.30	3.00	V	
	V	I _F = 60 A	-	2.89	3.80		
	V_{FM}	I _F = 30 A, T _J = 125 °C	-	2.14	2.44		
		I _F = 60 A, T _J = 125 °C	-	2.82	3.27		
Reverse leakage current		V _R = V _R rated	-	1.2	75	μΑ	
	I _{RM}	T _J = 125 °C, V _R = V _R rated	-	1.0	-	^	
		T _J = 150 °C, V _R = V _R rated	-	2.7	10	mA	

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 1 A dI _F /dt = 200 A/μs V _R = 30 V	-	51	-	ns
The verse recovery time	trr	T _J = 25 °C		-	134	-	113
		T _J = 125 °C		-	204	-	
Deals vecesses as weent		T _J = 25 °C	I _F = 50 A	-	12	-	^
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = - 200 A/μs V _R = 200 V	-	18	-	A
Reverse recovery charge	0	T _J = 25 °C		-	790	-	nC
	Q _{rr}	T _J = 125 °C		-	1770	-	IIC IIC
Junction capacitance	C _T	V _R = 1200 V		-	24	-	pF

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	В		-	-	0.46	
Junction to case, both legs conducting	R_{thJC}		-	-	0.23	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf.in)
Case style				SOT	-227	

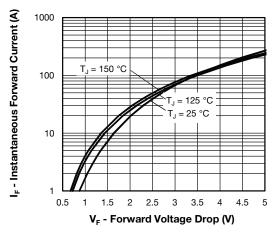


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

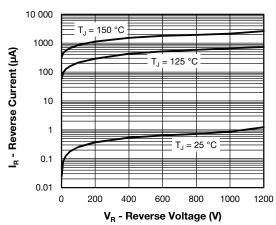


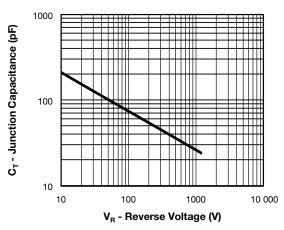
Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

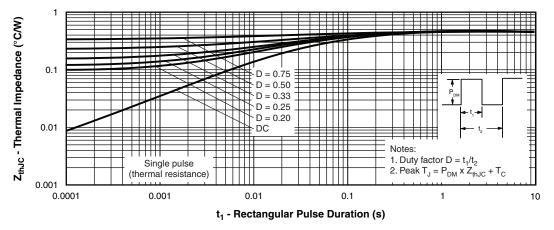


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

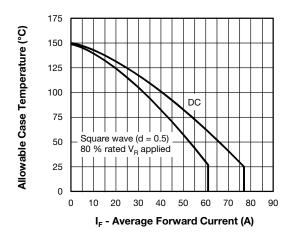


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

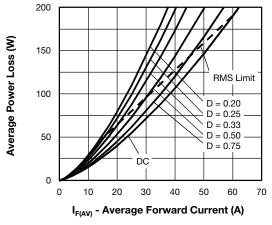


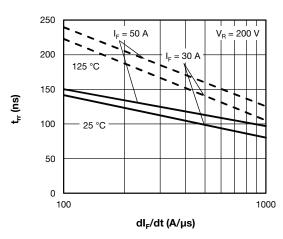
Fig. 6 - Forward Power Losses Characteristics (Per Leg)



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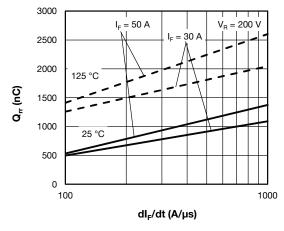


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

Fig. 8 - Typical Stored Charge vs. dl_F/dt

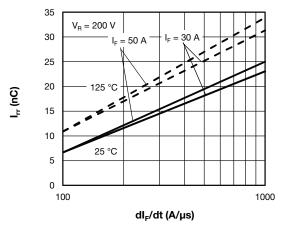


Fig. 9 - Typical Reverse Recovery Current vs. dI_F/dt

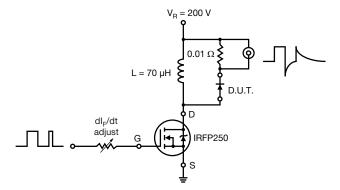


Fig. 10 - Reverse Recovery Parameter Test Circuit

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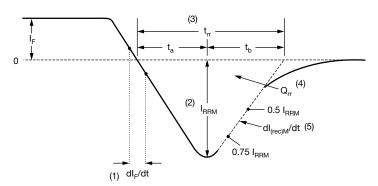
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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

1 - Vishay Semiconductors product

HEXFRED® family

Process designator (A = electron irradiated)

4 - Current rating (70 = 70 A)

5 - Circuit configuration (2 separate diodes, parallel pin-out)

Package indicator (SOT-227 standard insulated base)

7 - Voltage rating (120 = 1200 V)

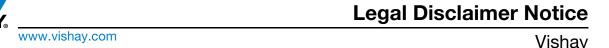
CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
2 separate diodes, parallel pin-out	F	Lead Assignment 4 0 0 3 3 1 0 0 2 1			

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